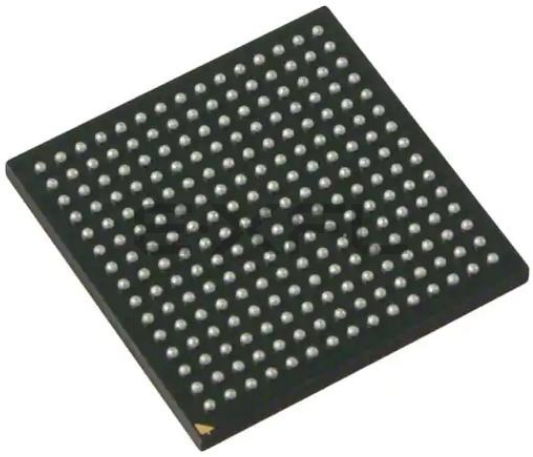

Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	1000
Number of Logic Elements/Cells	12800
Total RAM Bits	368640
Number of I/O	100
Number of Gates	-
Voltage - Supply	0.95V ~ 1.05V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	225-LFBGA, CSPBGA
Supplier Device Package	225-CSPBGA (13x13)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc7s15-2csga225c

Table 1: **Absolute Maximum Ratings(1) *(Cont'd)***

Symbol	Description	Min	Max	Units
V_{IN}(2)(3)(4)	I/O input voltage.	–0.4	V_{CCO} + 0.55	V
	I/O input voltage (when V_{CCO} = 3.3V) for V_{REF} and differential I/O standards except TMDS_33.(5)	–0.4	2.625	V
V_{CCBATT}	Key memory battery backup supply.	–0.5	2.0	V
XADC				
V_{CCADC}	XADC supply relative to GNDADC.	–0.5	2.0	V
V_{REFP}	XADC reference input relative to GNDADC.	–0.5	2.0	V
Temperature				
T_{STG}	Storage temperature (ambient).	–65	150	°C
T_{SOL}	Maximum soldering temperature for Pb/Sn component bodies.(6)	–	+220	°C
	Maximum soldering temperature for Pb-free component bodies.(6)	–	+260	°C
T_j	Maximum junction temperature.(6)	–	+125	°C

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.
2. The lower absolute voltage specification always applies.
3. For I/O operation, refer to the *7 Series FPGAs SelectIO Resources User Guide* (UG471) [Ref 3].
4. The maximum limit applies to DC signals. For maximum undershoot and overshoot AC specifications, see Table 4.
5. See Table 9 for TMDS_33 specifications.
6. For soldering guidelines and thermal considerations, see the *7 Series FPGA Packaging and Pinout Specification* (UG475) [Ref 4].

Table 2: **Recommended Operating Conditions(1)(2)**

Symbol	Description	Min	Typ	Max	Units
FPGA Logic					
V_{CCINT}(3)	For -2 and -1 (1.0V) devices: internal supply voltage.	0.95	1.00	1.05	V
	For -1L (0.95V) devices: internal supply voltage.	0.92	0.95	0.98	V
V_{CCAUX}	Auxiliary supply voltage.	1.71	1.80	1.89	V
V_{CCBRAM}(3)	For -2 and -1 (1.0V) devices: block RAM supply voltage.	0.95	1.00	1.05	V
	For -1L (0.95V) devices: block RAM supply voltage.	0.92	0.95	0.98	V
V_{CCO}(4)(5)	Supply voltage for HR I/O banks.	1.14	–	3.465	V
V_{IN}(6)	I/O input voltage.	–0.20	–	V_{CCO} + 0.20	V
	I/O input voltage (when V_{CCO} = 3.3V) for V_{REF} and differential I/O standards except TMDS_33.(7)	–0.20	–	2.625	V
I_{IN}(8)	Maximum current through any pin in a powered or unpowered bank when forward biasing the clamp diode.	–	–	10	mA
V_{CCBATT}(9)	Battery voltage.	1.0	–	1.89	V
XADC					
V_{CCADC}	XADC supply relative to GNDADC.	1.71	1.80	1.89	V
V_{REFP}	Externally supplied reference voltage.	1.20	1.25	1.30	V
Temperature					
T_j	Junction temperature operating range for commercial (C) temperature devices.	0	–	85	°C
	Junction temperature operating range for industrial (I) temperature devices.	–40	–	100	°C
	Junction temperature operating range for expanded (Q) temperature devices.	–40	–	125	°C

Notes:

1. All voltages are relative to ground.
2. For the design of the power distribution system consult the *7 Series FPGAs PCB Design Guide* (UG483) [Ref 5].
3. If V_{CCINT} and V_{CCBRAM} are operating at the same voltage, V_{CCINT} and V_{CCBRAM} should be connected to the same supply.
4. Configuration data is retained even if V_{CCO} drops to 0V.
5. Includes V_{CCO} of 1.2V, 1.35V, 1.5V, 1.8V, 2.5V, and 3.3V at ±5%.
6. The lower absolute voltage specification always applies.
7. See Table 9 for TMDS_33 specifications.
8. A total of 200 mA per bank should not be exceeded.
9. V_{CCBATT} is required only when using bitstream encryption. If battery is not used, connect V_{CCBATT} to either ground or V_{CCAUX}.

Table 3: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description	Min	Typ[1]	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost).	0.75	–	–	V
V_{DRI}	Data retention V_{CCAUX} voltage (below which configuration data might be lost).	1.5	–	–	V
I_{REF}	V_{REF} leakage current per pin.	–	–	15	µA
I_L	Input or output leakage current per pin (sample-tested).	–	–	15	µA
C_{IN}[2]	Die input capacitance at the pad.	–	–	8	pF
I_{RPU}	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 3.3V.	90	–	330	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 2.5V.	68	–	250	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.8V.	34	–	220	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.5V.	23	–	150	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.2V.	12	–	120	µA
I_{RPD}	Pad pull-down (when selected) at V_{IN} = 3.3V.	68	–	330	µA
I_{CCADC}	Analog supply current, analog circuits in powered up state.	–	–	25	mA
I_{BATT}[3]	Battery supply current.	–	–	150	nA
R_{IN_TERM}[4]	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 (UNTUNED_SPLIT_40).	28	40	55	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 (UNTUNED_SPLIT_50).	35	50	65	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 (UNTUNED_SPLIT_60).	44	60	83	Ω
n	Temperature diode ideality factor.	–	1.010	–	–
r	Temperature diode series resistance.	–	2	–	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. This measurement represents the die capacitance at the pad, not including the package.
3. Maximum value specified for worst case process at 25°C.
4. Termination resistance to a V_{CCO}/2 level.

Table 5: **Typical Quiescent Supply Current[(1)(2)(3)] *(Cont'd)***

Symbol	Description	Device	Speed Grade						Units
			1.0V					0.95V	
			-2C	-2I	-1C	-1I	-1Q	-1LI	
I_{CCOQ}	Quiescent V_{CCO} supply current.	XC7S6	1	1	1	1	1	1	mA
		XC7S15	1	1	1	1	1	1	mA
		XC7S25	1	1	1	1	1	1	mA
		XC7S50	1	1	1	1	1	1	mA
		XC7S75	4	4	4	4	4	4	mA
		XC7S100	4	4	4	4	4	4	mA
		XA7S6	N/A	1	N/A	1	1	N/A	mA
		XA7S15	N/A	1	N/A	1	1	N/A	mA
		XA7S25	N/A	1	N/A	1	1	N/A	mA
		XA7S50	N/A	1	N/A	1	1	N/A	mA
		XA7S75	N/A	4	N/A	4	4	N/A	mA
		XA7S100	N/A	4	N/A	4	4	N/A	mA
I_{CCAUXQ}	Quiescent V_{CCAUX} supply current.	XC7S6	10	10	10	10	10	10	mA
		XC7S15	10	10	10	10	10	10	mA
		XC7S25	13	13	13	13	13	13	mA
		XC7S50	22	22	22	22	22	20	mA
		XC7S75	43	43	43	43	43	43	mA
		XC7S100	43	43	43	43	43	43	mA
		XA7S6	N/A	10	N/A	10	10	N/A	mA
		XA7S15	N/A	10	N/A	10	10	N/A	mA
		XA7S25	N/A	13	N/A	13	13	N/A	mA
		XA7S50	N/A	22	N/A	22	22	N/A	mA
		XA7S75	N/A	43	N/A	43	43	N/A	mA
		XA7S100	N/A	43	N/A	43	43	N/A	mA

Table 6 shows the minimum current, in addition to I_{CCQ} maximum, that is required by Spartan-7 devices for proper power-on and configuration. If the current minimums shown in Table 6 are met, the device powers on after all four supplies have passed through their power-on reset threshold voltages. The FPGA must not be configured until after V_{CCINT} is applied. Once initialized and configured, use the *Xilinx Power Estimator* spreadsheet tool [Ref 6] to estimate current drain on these supplies.

Table 6: **Power-On Current**

Device	$I_{CCINTMIN}$	$I_{CCAUXMIN}$	I_{CCOMIN}	$I_{CCBRAMMIN}$	Units
XC7S6	I_{CCINTQ} + 120	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XC7S15	I_{CCINTQ} + 120	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XC7S25	I_{CCINTQ} + 120	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XC7S50	I_{CCINTQ} + 120	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XC7S75	I_{CCINTQ} + 300	I_{CCAUXQ} + 140	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XC7S100	I_{CCINTQ} + 300	I_{CCAUXQ} + 140	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XA7S6	I_{CCINTQ} + 120	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XA7S15	I_{CCINTQ} + 120	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XA7S25	I_{CCINTQ} + 120	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XA7S50	I_{CCINTQ} + 120	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XA7S75	I_{CCINTQ} + 300	I_{CCAUXQ} + 140	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA
XA7S100	I_{CCINTQ} + 300	I_{CCAUXQ} + 140	I_{CCOQ} + 40 mA per bank	$I_{CCBRAMQ}$ + 60	mA

Table 7: **Power Supply Ramp Time**

Symbol	Description	Conditions	Min	Max	Units
T_{VCCINT}	Ramp time from GND to 90% of V_{CCINT}.		0.2	50	ms
T_{VCCO}	Ramp time from GND to 90% of V_{CCO}.		0.2	50	ms
T_{VCCAUX}	Ramp time from GND to 90% of V_{CCAUX}.		0.2	50	ms
$T_{VCCBRAM}$	Ramp time from GND to 90% of V_{CCBRAM}.		0.2	50	ms
$T_{VCCO2VCCAUX}$	Allowed time per power cycle for $V_{CCO} - V_{CCAUX} > 2.625V$.	T_J = 125°C(1)	–	300	ms
		T_J = 100°C(1)	–	500	ms
		T_J = 85°C(1)	–	800	ms

Notes:

1. Based on 240,000 power cycles with a nominal V_{CCO} of 3.3V or 36,500 power cycles with a worst case V_{CCO} of 3.465V.

DC Input and Output Levels

Values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

Table 8: **SelectIO DC Input and Output Levels**(1)(2)(3)

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA, Max	mA, Min
HSTL_I	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8.00	–8.00
HSTL_I_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8.00	–8.00
HSTL_II	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	16.00	–16.00
HSTL_II_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	16.00	–16.00
HSUL_12	–0.300	V_{REF} – 0.130	V_{REF} + 0.130	V_{CCO} + 0.300	20% V_{CCO}	80% V_{CCO}	0.10	–0.10
LVCMOS12	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 4	Note 4
LVCMOS15	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	25% V_{CCO}	75% V_{CCO}	Note 5	Note 5
LVCMOS18	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	Note 6	Note 6
LVCMOS25	–0.300	0.7	1.700	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 5	Note 5
LVCMOS33	–0.300	0.8	2.000	3.450	0.400	V_{CCO} – 0.400	Note 5	Note 5
LVTTL	–0.300	0.8	2.000	3.450	0.400	2.400	Note 6	Note 6
MOBILE_DDR	–0.300	20% V_{CCO}	80% V_{CCO}	V_{CCO} + 0.300	10% V_{CCO}	90% V_{CCO}	0.10	–0.10
PCI33_3	–0.400	30% V_{CCO}	50% V_{CCO}	V_{CCO} + 0.500	10% V_{CCO}	90% V_{CCO}	1.50	–0.50
SSTL135	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	13.00	–13.00
SSTL135_R	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	8.90	–8.90
SSTL15	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	13.00	–13.00
SSTL15_R	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	8.90	–8.90
SSTL18_I	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.470	V_{CCO}/2 + 0.470	8.00	–8.00
SSTL18_II	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.600	V_{CCO}/2 + 0.600	13.40	–13.40

Notes:

1. Tested according to relevant specifications.
2. 3.3V and 2.5V standards are only supported in HR I/O banks.
3. For detailed interface specific DC voltage levels, see the *7 Series FPGAs SelectIO Resources User Guide* (UG471) [Ref 3].
4. Supported drive strengths of 4, 8, or 12 mA in HR I/O banks.
5. Supported drive strengths of 4, 8, 12, or 16 mA in HR I/O banks.
6. Supported drive strengths of 4, 8, 12, 16, or 24 mA in HR I/O banks.

Table 9: **Differential SelectIO DC Input and Output Levels**

I/O Standard	V_{ICM}[1]			V_{ID}[2]			V_{OCM}[3]			V_{OD}[4]		
	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max
BLVDS_25	0.300	1.200	1.425	0.100	–	–	–	1.250	–	Note 5		
MINI_LVDS_25	0.300	1.200	V_{CCAUX}	0.200	0.400	0.600	1.000	1.200	1.400	0.300	0.450	0.600
PPDS_25	0.200	0.900	V_{CCAUX}	0.100	0.250	0.400	0.500	0.950	1.400	0.100	0.250	0.400
RSDS_25	0.300	0.900	1.500	0.100	0.350	0.600	1.000	1.200	1.400	0.100	0.350	0.600
TMDS_33	2.700	2.965	3.230	0.150	0.675	1.200	V_{CCO} – 0.405	V_{CCO} – 0.300	V_{CCO} – 0.190	0.400	0.600	0.800

Notes:

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage (Q – $\overline{Q}$).
3. V_{OCM} is the output common mode voltage.
4. V_{OD} is the output differential voltage (Q – $\overline{Q}$).
5. V_{OD} for BLVDS will vary significantly depending on topology and loading.

Table 10: **Complementary Differential SelectIO DC Input and Output Levels**

I/O Standard	V_{ICM}[1]			V_{ID}[2]		V_{OL}[3]	V_{OH}[4]	I_{OL}	I_{OH}
	V, Min	V, Typ	V, Max	V, Min	V, Max	V, Max	V, Min	mA, Max	mA, Min
DIFF_HSTL_I	0.300	0.750	1.125	0.100	–	0.400	V_{CCO} – 0.400	8.00	–8.00
DIFF_HSTL_I_18	0.300	0.900	1.425	0.100	–	0.400	V_{CCO} – 0.400	8.00	–8.00
DIFF_HSTL_II	0.300	0.750	1.125	0.100	–	0.400	V_{CCO} – 0.400	16.00	–16.00
DIFF_HSTL_II_18	0.300	0.900	1.425	0.100	–	0.400	V_{CCO} – 0.400	16.00	–16.00
DIFF_HSUL_12	0.300	0.600	0.850	0.100	–	20% V_{CCO}	80% V_{CCO}	0.100	–0.100
DIFF_MOBILE_DDR	0.300	0.900	1.425	0.100	–	10% V_{CCO}	90% V_{CCO}	0.100	–0.100
DIFF_SSTL135	0.300	0.675	1.000	0.100	–	(V_{CCO}/2) – 0.150	(V_{CCO}/2) + 0.150	13.0	–13.0
DIFF_SSTL135_R	0.300	0.675	1.000	0.100	–	(V_{CCO}/2) – 0.150	(V_{CCO}/2) + 0.150	8.9	–8.9
DIFF_SSTL15	0.300	0.750	1.125	0.100	–	(V_{CCO}/2) – 0.175	(V_{CCO}/2) + 0.175	13.0	–13.0
DIFF_SSTL15_R	0.300	0.750	1.125	0.100	–	(V_{CCO}/2) – 0.175	(V_{CCO}/2) + 0.175	8.9	–8.9
DIFF_SSTL18_I	0.300	0.900	1.425	0.100	–	(V_{CCO}/2) – 0.470	(V_{CCO}/2) + 0.470	8.00	–8.00
DIFF_SSTL18_II	0.300	0.900	1.425	0.100	–	(V_{CCO}/2) – 0.600	(V_{CCO}/2) + 0.600	13.4	–13.4

Notes:

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage (Q – $\overline{Q}$).
3. V_{OL} is the single-ended low-output voltage.
4. V_{OH} is the single-ended high-output voltage.

Table 15: **Networking Applications Interface Performances *(Cont'd)***

Description	V_{CCINT} Operating Voltage, Speed Grade, and Temperature Range			Units
	1.0V		0.95V	
	-2C/-2I	-1C/-1I/-1Q	-1LI	
DDR LVDS receiver(1)	1250	950	950	Mb/s

Notes:

1. LVDS receivers are typically bounded with certain applications where specific dynamic phase-alignment (DPA) algorithms dominate deterministic performance.

Table 16: **Maximum Physical Interface (PHY) Rate for Memory Interface IP available with the Memory Interface Generator(1)**

Memory Standard	V_{CCINT} Operating Voltage, Speed Grade, and Temperature Range			Units
	1.0V		0.95V	
	-2C/-2I	-1C/-1I/-1Q	-1LI	
4:1 Memory Controllers				
DDR3	800(2)	667	667	Mb/s
DDR3L	800(2)	667	667	Mb/s
DDR2	800(2)	667	667	Mb/s
2:1 Memory Controllers				
DDR3	800(2)	667	667	Mb/s
DDR3L	800(2)	667	667	Mb/s
DDR2	800(2)	667	667	Mb/s
LPDDR2	667	533	533	Mb/s

Notes:

1. V_{REF} tracking is required. For more information, see the *Zynq-7000 AP SoC and 7 Series FPGAs Memory Interface Solutions User Guide* (UG586) [Ref 7].
2. The maximum PHY rate is 667 Mb/s in the FTGB196 package.

IOB Pad Input/Output/3-State

Table 17 summarizes the values of standard-specific data input delay adjustments, output delays terminating at pads (based on standard) and 3-state delays.

- T_{IOPI} is described as the delay from IOB pad through the input buffer to the I-pin of an IOB pad. The delay varies depending on the capability of the SelectIO input buffer.
- T_{IOOP} is described as the delay from the O pin to the IOB pad through the output buffer of an IOB pad. The delay varies depending on the capability of the SelectIO output buffer.
- T_{IOTP} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is disabled. The delay varies depending on the SelectIO capability of the output buffer. In HR I/O banks, the IN_TERM termination turn-on time is always faster than T_{IOTP} when the INTERMDISABLE pin is used.

Table 17: **IOB High Range (HR) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	V_{CCINT} Operating Voltage and Speed Grade									
	1.0V		0.95V	1.0V		0.95V	1.0V		0.95V	
	-2	-1	-1L	-2	-1	-1L	-2	-1	-1L	
HSTL_II_18_F	0.75	0.81	0.81	1.24	1.49	1.49	1.27	1.51	1.51	ns
DIFF_HSTL_I_F	0.76	0.83	0.83	1.30	1.56	1.56	1.33	1.57	1.57	ns
DIFF_HSTL_II_F	0.76	0.83	0.83	1.33	1.59	1.59	1.36	1.60	1.60	ns
DIFF_HSTL_I_18_F	0.79	0.86	0.86	1.33	1.59	1.59	1.36	1.60	1.60	ns
DIFF_HSTL_II_18_F	0.78	0.85	0.85	1.33	1.59	1.59	1.36	1.60	1.60	ns
LVCMOS33_S4	1.34	1.41	1.41	3.93	4.18	4.18	3.96	4.20	4.20	ns
LVCMOS33_S8	1.34	1.41	1.41	3.65	3.90	3.90	3.68	3.91	3.91	ns
LVCMOS33_S12	1.34	1.41	1.41	3.21	3.46	3.46	3.24	3.48	3.48	ns
LVCMOS33_S16	1.34	1.41	1.41	3.52	3.77	3.77	3.55	3.79	3.79	ns
LVCMOS33_F4	1.34	1.41	1.41	3.38	3.64	3.64	3.41	3.65	3.65	ns
LVCMOS33_F8	1.34	1.41	1.41	2.87	3.12	3.12	2.90	3.13	3.13	ns
LVCMOS33_F12	1.34	1.41	1.41	2.68	2.93	2.93	2.71	2.95	2.95	ns
LVCMOS33_F16	1.34	1.41	1.41	2.68	2.93	2.93	2.71	2.95	2.95	ns
LVCMOS25_S4	1.20	1.27	1.27	3.26	3.51	3.51	3.29	3.52	3.52	ns
LVCMOS25_S8	1.20	1.27	1.27	3.01	3.26	3.26	3.04	3.27	3.27	ns
LVCMOS25_S12	1.20	1.27	1.27	2.60	2.85	2.85	2.63	2.87	2.87	ns
LVCMOS25_S16	1.20	1.27	1.27	2.94	3.20	3.20	2.97	3.21	3.21	ns
LVCMOS25_F4	1.20	1.27	1.27	2.87	3.12	3.12	2.90	3.13	3.13	ns
LVCMOS25_F8	1.20	1.27	1.27	2.30	2.56	2.56	2.33	2.57	2.57	ns
LVCMOS25_F12	1.20	1.27	1.27	2.29	2.54	2.54	2.32	2.55	2.55	ns
LVCMOS25_F16	1.20	1.27	1.27	2.13	2.39	2.39	2.16	2.40	2.40	ns
LVCMOS18_S4	0.83	0.89	0.89	1.74	1.99	1.99	1.77	2.01	2.01	ns
LVCMOS18_S8	0.83	0.89	0.89	2.30	2.56	2.56	2.33	2.57	2.57	ns
LVCMOS18_S12	0.83	0.89	0.89	2.30	2.56	2.56	2.33	2.57	2.57	ns
LVCMOS18_S16	0.83	0.89	0.89	1.65	1.90	1.90	1.68	1.91	1.91	ns
LVCMOS18_S24	0.83	0.89	0.89	1.72	1.98	1.98	1.75	1.99	1.99	ns
LVCMOS18_F4	0.83	0.89	0.89	1.57	1.82	1.82	1.60	1.84	1.84	ns
LVCMOS18_F8	0.83	0.89	0.89	1.80	2.06	2.06	1.83	2.07	2.07	ns
LVCMOS18_F12	0.83	0.89	0.89	1.80	2.06	2.06	1.83	2.07	2.07	ns
LVCMOS18_F16	0.83	0.89	0.89	1.52	1.77	1.77	1.55	1.79	1.79	ns
LVCMOS18_F24	0.83	0.89	0.89	1.46	1.71	1.71	1.49	1.73	1.73	ns
LVCMOS15_S4	0.86	0.93	0.93	2.18	2.43	2.43	2.21	2.45	2.45	ns
LVCMOS15_S8	0.86	0.93	0.93	2.21	2.46	2.46	2.24	2.48	2.48	ns
LVCMOS15_S12	0.86	0.93	0.93	1.71	1.96	1.96	1.74	1.98	1.98	ns
LVCMOS15_S16	0.86	0.93	0.93	1.71	1.96	1.96	1.74	1.98	1.98	ns
LVCMOS15_F4	0.86	0.93	0.93	1.97	2.23	2.23	2.00	2.24	2.24	ns

Table 18: **IOB 3-state Output Switching Characteristics**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T_{IOTPHZ}	T input to pad high-impedance.	2.19	2.37	2.37	ns
$T_{IOIBUFDISABLE}$	IBUF turn-on time from IBUFDISABLE to O output.	2.30	2.60	2.60	ns

Output Delay Measurements

Output delays are measured with short output traces. Standard termination was used for all testing. The propagation delay of the trace is characterized separately and subtracted from the final measurement, and is therefore not included in the generalized test setups shown in Figure 1 and Figure 2.

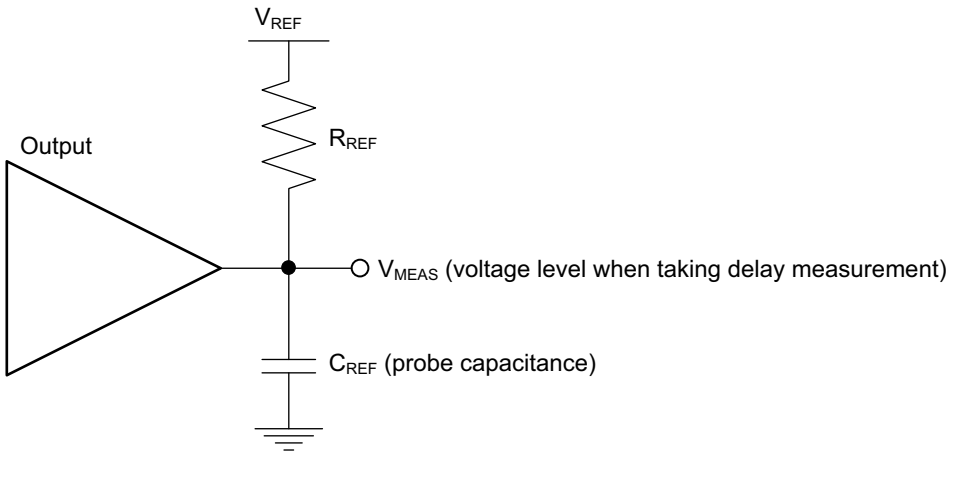

Figure 1: **Single-ended Test Setup**

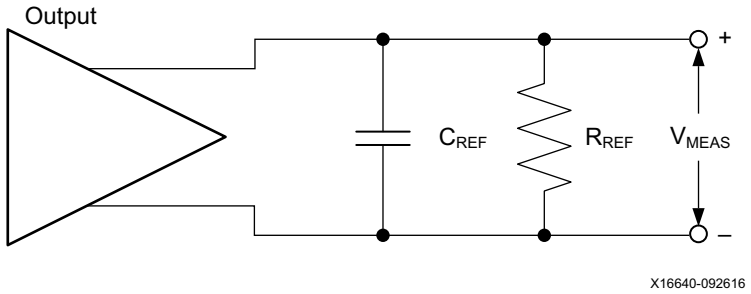

Figure 2: **Differential Test Setup**

Parameters V_{REF}, R_{REF}, C_{REF}, and V_{MEAS} fully describe the test conditions for each I/O standard. The most accurate prediction of propagation delay in any given application can be obtained through IBIS simulation, using this method:

1. Simulate the output driver of choice into the generalized test setup using values from Table 20.
2. Record the time to V_{MEAS}.
3. Simulate the output driver of choice into the actual PCB trace and load using the appropriate IBIS model or capacitance value to represent the load.
4. Record the time to V_{MEAS}.
5. Compare the results of step 2 and step 4. The increase or decrease in delay yields the actual propagation delay of the PCB trace.

Table 30: **Block RAM and FIFO Switching Characteristics *(Cont'd)***

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
$T_{RDCK\_DI\_ECC\_FIFO}$/ $T_{RCKD\_DI\_ECC\_FIFO}$	DIN inputs with FIFO ECC in standard mode.(8)	1.15/0.59	1.32/0.64	1.32/0.64	ns, Min
$T_{RCCK\_INJECTBITERR}$/ $T_{RCKC\_INJECTBITERR}$	Inject single/double bit error in ECC mode.	0.64/0.37	0.74/0.40	0.74/0.40	ns, Min
T_{RCCK_EN}/T_{RCKC_EN}	Block RAM enable (EN) input.	0.39/0.21	0.45/0.23	0.45/0.23	ns, Min
T_{RCCK_REGCE}/ T_{RCKC_REGCE}	CE input of output register.	0.29/0.15	0.36/0.16	0.36/0.16	ns, Min
T_{RCCK_RSTREG}/ T_{RCKC_RSTREG}	Synchronous RSTREG input.	0.32/0.07	0.35/0.07	0.35/0.07	ns, Min
T_{RCCK_RSTRAM}/ T_{RCKC_RSTRAM}	Synchronous RSTRAM input.	0.34/0.43	0.36/0.46	0.36/0.46	ns, Min
T_{RCCK_WEA}/T_{RCKC_WEA}	Write enable (WE) input (block RAM only).	0.48/0.19	0.54/0.20	0.54/0.20	ns, Min
T_{RCCK_WREN}/ T_{RCKC_WREN}	WREN FIFO inputs.	0.46/0.35	0.47/0.43	0.47/0.43	ns, Min
T_{RCCK_RDEN}/ T_{RCKC_RDEN}	RDEN FIFO inputs.	0.43/0.35	0.43/0.43	0.43/0.43	ns, Min
Reset Delays					
T_{RCO_FLAGS}	Reset RST to FIFO flags/pointers.(9)	0.98	1.10	1.10	ns, Max
T_{RREC_RST}/T_{RREM_RST}	FIFO reset recovery and removal timing.(10)	2.07/–0.81	2.37/–0.81	2.37/–0.81	ns, Max
Maximum Frequency					
$F_{MAX\_BRAM\_WF\_NC}$	Block RAM (write first and no change modes) when not in SDP RF mode.	460.83	388.20	388.20	MHz
$F_{MAX\_BRAM\_RF\_PERFORMANCE}$	Block RAM (read first, performance mode) when in SDP RF mode but no address overlap between port A and port B.	460.83	388.20	388.20	MHz
$F_{MAX\_BRAM\_RF\_DELAYED\_WRITE}$	Block RAM (read first, delayed write mode) when in SDP RF mode and there is possibility of overlap between port A and port B addresses.	404.53	339.67	339.67	MHz
$F_{MAX\_CAS\_WF\_NC}$	Block RAM cascade (write first, no change mode) when cascade but not in RF mode.	418.59	345.78	345.78	MHz
$F_{MAX\_CAS\_RF\_PERFORMANCE}$	Block RAM cascade (read first, performance mode) when in cascade with RF mode and no possibility of address overlap/one port is disabled.	418.59	345.78	345.78	MHz

Table 31: **DSP48E1 Switching Characteristics *(Cont'd)***

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
$T_{DSPDO\_PCIN\_CARRYCASCOUT}$	PCIN input to CARRYCASCOUT output.	1.56	1.85	1.85	ns
Clock to Outs from Output Register Clock to Output Pins					
$T_{DSPCKO\_P\_PREG}$	CLK PREG to P output.	0.37	0.44	0.44	ns
$T_{DSPCKO\_CARRYCASCOUT\_PREG}$	CLK PREG to CARRYCASCOUT output.	0.59	0.69	0.69	ns
Clock to Outs from Pipeline Register Clock to Output Pins					
$T_{DSPCKO\_P\_MREG}$	CLK MREG to P output.	1.93	2.31	2.31	ns
$T_{DSPCKO\_CARRYCASCOUT\_MREG}$	CLK MREG to CARRYCASCOUT output.	2.21	2.64	2.64	ns
$T_{DSPCKO\_P\_ADREG\_MULT}$	CLK ADREG to P output using multiplier.	3.10	3.69	3.69	ns
$T_{DSPCKO\_CARRYCASCOUT\_ADREG\_MULT}$	CLK ADREG to CARRYCASCOUT output using multiplier.	3.38	4.02	4.02	ns
Clock to Outs from Input Register Clock to Output Pins					
$T_{DSPCKO\_P\_AREG\_MULT}$	CLK AREG to P output using multiplier.	4.51	5.37	5.37	ns
$T_{DSPCKO\_P\_BREG}$	CLK BREG to P output not using multiplier.	1.87	2.22	2.22	ns
$T_{DSPCKO\_P\_CREG}$	CLK CREG to P output not using multiplier.	1.93	2.30	2.30	ns
$T_{DSPCKO\_P\_DREG\_MULT}$	CLK DREG to P output using multiplier.	4.48	5.32	5.32	ns
Clock to Outs from Input Register Clock to Cascading Output Pins					
$T_{DSPCKO\_\{ACOUT;\ BCOUT\}\_\{AREG;\ BREG\}}$	CLK (ACOUT, BCOUT) to {A,B} register output.	0.73	0.87	0.87	ns
$T_{DSPCKO\_CARRYCASCOUT\_\{AREG,\ BREG\}\_MULT}$	CLK (AREG, BREG) to CARRYCASCOUT output using multiplier.	4.79	5.70	5.70	ns
$T_{DSPCKO\_CARRYCASCOUT\_\ BREG}$	CLK BREG to CARRYCASCOUT output not using multiplier.	2.15	2.55	2.55	ns
$T_{DSPCKO\_CARRYCASCOUT\_\ DREG\_MULT}$	CLK DREG to CARRYCASCOUT output using multiplier.	4.76	5.65	5.65	ns
$T_{DSPCKO\_CARRYCASCOUT\_\ CREG}$	CLK CREG to CARRYCASCOUT output.	2.21	2.63	2.63	ns
Maximum Frequency					
F_{MAX}	With all registers used.	550.66	464.25	464.25	MHz
F_{MAX_PATDET}	With pattern detector.	465.77	392.93	392.93	MHz
$F_{MAX\_MULT\_NOMREG}$	Two register multiply without MREG.	305.62	257.47	257.47	MHz
$F_{MAX\_MULT\_NOMREG\_PATDET}$	Two register multiply without MREG with pattern detect.	277.62	233.92	233.92	MHz
$F_{MAX\_PREADD\_MULT\_NOADREG}$	Without ADREG.	346.26	290.44	290.44	MHz
$F_{MAX\_PREADD\_MULT\_NOADREG\_PATDET}$	Without ADREG with pattern detect.	346.26	290.44	290.44	MHz
$F_{MAX\_NOPIPELINEREG}$	Without pipeline registers (MREG, ADREG).	227.01	190.69	190.69	MHz
$F_{MAX\_NOPIPELINEREG\_PATDET}$	Without pipeline registers (MREG, ADREG) with pattern detect.	211.15	177.43	177.43	MHz

Table 35: **Horizontal Clock Buffer Switching Characteristics (BUFH)**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T_{BHCKO_O}	BUFH delay from I to O.	0.11	0.13	0.13	ns
T_{BHCCK_CE}/ T_{BHCKC_CE}	CE pin setup and hold.	0.22/0.15	0.28/0.21	0.28/0.21	ns
Maximum Frequency					
F_{MAX_BUFH}	Horizontal clock buffer (BUFH).	628.00	464.00	464.00	MHz

Table 36: **Duty Cycle Distortion and Clock-Tree Skew**

Symbol	Description	Device	V_{CCINT} Operating Voltage and Speed Grade			Units
			1.0V		0.95V	
			-2	-1	-1L	
T_{DCD_CLK}	Global clock tree duty-cycle distortion.(1)	All	0.20	0.20	0.20	ns
T_{CKSKEW}	Global clock tree skew.(2)	XC7S6	0.05	0.06	0.06	ns
		XC7S15	0.05	0.06	0.06	ns
		XC7S25	0.26	0.26	0.26	ns
		XC7S50	0.26	0.26	0.26	ns
		XC7S75	0.33	0.36	0.36	ns
		XC7S100	0.33	0.36	0.36	ns
		XA7S6	0.05	0.06	N/A	ns
		XA7S15	0.05	0.06	N/A	ns
		XA7S25	0.26	0.26	N/A	ns
		XA7S50	0.26	0.26	N/A	ns
		XA7S75	0.33	0.36	N/A	ns
		XA7S100	0.33	0.36	N/A	ns
T_{DCD_BUFIO}	I/O clock tree duty cycle distortion.	All	0.14	0.14	0.14	ns
$T_{BUFIOSKEW}$	I/O clock tree skew across one clock region.	All	0.03	0.03	0.03	ns
T_{DCD_BUFR}	Regional clock tree duty cycle distortion.	All	0.18	0.18	0.18	ns

Notes:

1. These parameters represent the worst-case duty cycle distortion observable at the I/O flip flops. For all I/O standards, IBIS can be used to calculate any additional duty cycle distortion that might be caused by asymmetrical rise/fall times.
2. The T_{CKSKEW} value represents the worst-case clock-tree skew observable between sequential I/O elements. Significantly less clock-tree skew exists for I/O registers that are close to each other and fed by the same or adjacent clock-tree branches. Use the Xilinx timing analysis tools to evaluate clock skew specific to your application.

Table 37: **MMCM Specification *(Cont'd)***

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
$T_{MMCMDCK\_PSINCDEC}$/ $T_{MMCMCKD\_PSINCDEC}$	Setup and hold of phase-shift increment/decrement.	1.04/0.00	1.04/0.00	1.04/0.00	ns
$T_{MMCMCKO\_PSDONE}$	Phase shift clock-to-out of PSDONE.	0.68	0.81	0.81	ns
Dynamic Reconfiguration Port (DRP) for MMCM Before and After DCLK					
$T_{MMCMDCK\_DADDR}$/ $T_{MMCMCKD\_DADDR}$	DADDR setup/hold.	1.40/0.15	1.63/0.15	1.63/0.15	ns, Min
$T_{MMCMDCK\_DI}$/ $T_{MMCMCKD\_DI}$	DI setup/hold.	1.40/0.15	1.63/0.15	1.63/0.15	ns, Min
$T_{MMCMDCK\_DEN}$/ $T_{MMCMCKD\_DEN}$	DEN setup/hold.	1.97/0.00	2.29/0.00	2.29/0.00	ns, Min
$T_{MMCMDCK\_DWE}$/ $T_{MMCMCKD\_DWE}$	DWE setup/hold.	1.40/0.15	1.63/0.15	1.63/0.15	ns, Min
$T_{MMCMCKO\_DRDY}$	CLK to out of DRDY.	0.72	0.99	0.99	ns, Max
F_{DCK}	DCLK frequency.	200.00	200.00	200.00	MHz, Max

Notes:

1. The MMCM does not filter typical spread-spectrum input clocks because they are usually far below the bandwidth filter frequencies.
2. The static offset is measured between any MMCM outputs with identical phase.
3. Values for this parameter are available in the *Clocking Wizard* [Ref 8].
4. Includes global clock buffer.
5. Calculated as F_{VCO}/128 assuming output duty cycle is 50%.
6. When CLKOUT4_CASCADE = TRUE, MMCM_F_{OUTMIN} is 0.036 MHz.

PLL Switching Characteristics

Table 38: **PLL Specification**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
PLL_F_{INMAX}	Maximum input clock frequency.	800.00	800.00	800.00	MHz
PLL_F_{INMIN}	Minimum input clock frequency.	19.00	19.00	19.00	MHz
PLL_$F_{INJITTER}$	Maximum input clock period jitter.	< 20% of clock input period or 1 ns Max			
PLL_F_{INDUTY}	Allowable input duty cycle: 19—49 MHz.	25	25	25	%
	Allowable input duty cycle: 50—199 MHz.	30	30	30	%
	Allowable input duty cycle: 200—399 MHz.	35	35	35	%
	Allowable input duty cycle: 400—499 MHz.	40	40	40	%
	Allowable input duty cycle: >500 MHz.	45	45	45	%
PLL_F_{VCOMIN}	Minimum PLL VCO frequency.	800.00	800.00	800.00	MHz
PLL_F_{VCOMAX}	Maximum PLL VCO frequency.	1866.00	1600.00	1600.00	MHz

Device Pin-to-Pin Output Parameter Guidelines

Table 39: **Clock-Capable Clock Input to Output Delay Without MMCM/PLL (Near Clock Region)[1]**

Symbol	Description	Device	V_{CCINT} Operating Voltage and Speed Grade			Units
			1.0V		0.95V	
			-2	-1	-1L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, *without* MMCM/PLL.						
T_{ICKOF}	Clock-capable clock input and OUTFF at pins/banks closest to the BUFGs *without* MMCM/PLL (near clock region).[2]	XC7S6	5.55	6.50	6.50	ns
		XC7S15	5.55	6.50	6.50	ns
		XC7S25	5.55	6.44	6.44	ns
		XC7S50	5.71	6.62	6.62	ns
		XC7S75	5.73	6.71	6.71	ns
		XC7S100	5.73	6.71	6.71	ns
		XA7S6	5.55	6.50	N/A	ns
		XA7S15	5.55	6.50	N/A	ns
		XA7S25	5.55	6.44	N/A	ns
		XA7S50	5.71	6.62	N/A	ns
		XA7S75	5.73	6.71	N/A	ns
		XA7S100	5.73	6.71	N/A	ns

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. Refer to the *Die Level Bank Numbering Overview* section of the *7 Series FPGA Packaging and Pinout Specification* (UG475) [Ref 4].

Table 40: **Clock-Capable Clock Input to Output Delay Without MMCM/PLL (Far Clock Region)[1]**

Symbol	Description	Device	V_{CCINT} Operating Voltage and Speed Grade			Units
			1.0V		0.95V	
			-2	-1	-1L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, *without* MMCM/PLL.						
$T_{ICKOFFAR}$	Clock-capable clock input and OUTFF at pins/banks farthest from the BUFGs *without* MMCM/PLL (far clock region).[2]	XC7S6	5.55	6.50	6.50	ns
		XC7S15	5.55	6.50	6.50	ns
		XC7S25	5.55	6.44	6.44	ns
		XC7S50	5.71	6.62	6.62	ns
		XC7S75	6.01	7.02	7.02	ns
		XC7S100	6.01	7.02	7.02	ns
		XA7S6	5.55	6.50	N/A	ns
		XA7S15	5.55	6.50	N/A	ns
		XA7S25	5.55	6.44	N/A	ns
		XA7S50	5.71	6.62	N/A	ns
		XA7S75	6.01	7.02	N/A	ns
		XA7S100	6.01	7.02	N/A	ns

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. Refer to the *Die Level Bank Numbering Overview* section of the *7 Series FPGA Packaging and Pinout Specification* (UG475) [Ref 4].

Table 42: **Clock-Capable Clock Input to Output Delay With PLL(1)**

Symbol	Description	Device	V_{CCINT} Operating Voltage and Speed Grade			Units
			1.0V		0.95V	
			-2	-1	-1L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, *with* PLL.						
$T_{ICKOFPLLCC}$	Clock-capable clock input and OUTFF *with* PLL.(2)	XC7S6	0.85	0.85	0.85	ns
		XC7S15	0.85	0.85	0.85	ns
		XC7S25	0.83	0.83	0.83	ns
		XC7S50	0.83	0.83	0.83	ns
		XC7S75	0.83	0.83	0.83	ns
		XC7S100	0.83	0.83	0.83	ns
		XA7S6	0.85	0.85	N/A	ns
		XA7S15	0.85	0.85	N/A	ns
		XA7S25	0.83	0.83	N/A	ns
		XA7S50	0.83	0.83	N/A	ns
		XA7S75	0.83	0.83	N/A	ns
		XA7S100	0.83	0.83	N/A	ns

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. PLL output jitter is already included in the timing calculation.

Table 43: **Pin-to-Pin, Clock-to-Out using BUFIO**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, with BUFIO.					
$T_{ICKOFCS}$	Clock to out of I/O clock.	5.61	6.64	6.64	ns

Table 48: **Sample Window**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T_{SAMP}	Sampling error at receiver pins.(1)	0.64	0.70	0.70	ns
T_{SAMP_BUFIO}	Sampling error at receiver pins using BUFIO.(2)	0.40	0.46	0.46	ns

Notes:

1. This parameter indicates the total sampling error of the Spartan-7 FPGAs DDR input registers, measured across voltage, temperature, and process. The characterization methodology uses the MMCM to capture the DDR input registers' edges of operation. These measurements include:
   - CLK0 MMCM jitter
   - MMCM accuracy (phase offset)
   - MMCM phase shift resolution

   These measurements do not include package or clock tree skew.
2. This parameter indicates the total sampling error of the Spartan-7 FPGAs DDR input registers, measured across voltage, temperature, and process. The characterization methodology uses the BUFIO clock network and IDELAY to capture the DDR input registers' edges of operation. These measurements do not include package or clock tree skew.

XADC Specifications

The *7 Series FPGAs Overview* (DS180) [Ref 1] and *XA Spartan-7 Automotive FPGA Data Sheet: Overview* (DS171) [Ref 2] list the devices that contain a 7 series XADC dual 12-Bit 1 MSPS analog-to-digital converter.

Table 50: **XADC Specifications**

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
V_{CCADC} = 1.8V ± 5%, V_{REFP} = 1.25V, V_{REFN} = 0V, ADCCLK = 26 MHz, –55°C ≤ T_j ≤ 125°C. Typical values at T_j = +40°C.						
ADC Accuracy(1)						
Resolution			12	–	–	Bits
Integral nonlinearity(2)	INL	–40°C ≤ T_j ≤ 100°C	–	–	±2	LSBs
		–55°C ≤ T_j < –40°C; 100°C < T_j ≤ 125°C	–	–	±3	LSBs
Differential nonlinearity	DNL	No missing codes, guaranteed monotonic.	–	–	±1	LSBs
Offset error	Unipolar	–40°C ≤ T_j ≤ 100°C	–	–	±8	LSBs
		–55°C ≤ T_j < –40°C; 100°C < T_j ≤ 125°C	–	–	±12	LSBs
	Bipolar	–55°C ≤ T_j ≤ 125°C	–	–	±4	LSBs
Gain error			–	–	±0.5	%
Offset matching			–	–	4	LSBs
Gain matching			–	–	0.3	%
Sample rate			–	–	1	MS/s
Signal to noise ratio(2)	SNR	F_{SAMPLE} = 500 KS/s, F_{IN} = 20 kHz	60	–	–	dB
RMS code noise		External 1.25V reference.	–	–	2	LSBs
		On-chip reference.	–	3	–	LSBs
Total harmonic distortion(2)	THD	F_{SAMPLE} = 500 KS/s, F_{IN} = 20 kHz	70	–	–	dB
Analog Inputs(3)						
ADC input ranges		Unipolar operation.	0	–	1	V
		Bipolar operation.	–0.5	–	+0.5	V
		Unipolar common mode range (FS input).	0	–	+0.5	V
		Bipolar common mode range (FS input).	+0.5	–	+0.6	V
Maximum external channel input ranges		Adjacent analog channels set within these ranges should not corrupt measurements on adjacent channels.	–0.1	–	V_{CCADC}	V
Full-resolution bandwidth	FRBW	Auxiliary channel full resolution bandwidth.	250	–	–	kHz
On-chip Sensors						
Temperature sensor error		–40°C ≤ T_j ≤ 100°C	–	–	±4	°C
		–55°C ≤ T_j < –40°C; 100°C < T_j ≤ 125°C	–	–	±6	°C
Supply sensor error		–40°C ≤ T_j ≤ 100°C	–	–	±1	%
		–55°C ≤ T_j < –40°C; 100°C < T_j ≤ 125°C	–	–	±2	%